| Part Number | | Customer | |

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.20 mm	
	2.0	Primary Flat Orientation	{110}+/- 1.0 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	368.00 +/- 5.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<1.00μm	ADE, 100%
	7.0	Bow	<30.00μm	ADE to ASTM F534, 20%
	8.0	Warp	<30.00μm	ADE to ASTM F657, 20%
	9.0	Edge Chips	None	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
	11.0	Flatness (SBIR)	<1um, 15mm X 15mm. No partials.	
	12.0	Front Surface Quality	Polished. No Particles >10um	
HandleSilicon	13.0	Handle Silicon Raw Material	Prime Silicon	
	14.0	Handle Growth Method	CZ	Wafer Vendor
	15.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	16.0	Handle Thickness	368.00 +/- 5.00 μm	ADE, 100%
	17.0	Handle Doping Type	N	Wafer Vendor
	18.0	Handle Dopant	Phosphorous	Wafer Vendor
	19.0	Handle Resistivity	1~ 3 Ohmcm	Wafer Vendor
	20.0	Backside Finish	Polished, with lasermarking. Light handling scrtaches.	Guaranteed by process
	21.0	Surface Haze	none	Bright Light, 100% (note 2)

Part Number			Customer		

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:

Additional Information